

## 20V N-Channel Power MOSFET

**UM2302S SOT23-3**  
**UM2302P SOT323**

### General Description

The UM2302 is a low threshold N-channel MOSFET, have extremely low on-resistance. This benefit provides the designer with an extremely efficient device for use in battery and load management applications. The device uses a space-saving, small-outline SOT23-3 or SOT323 package.

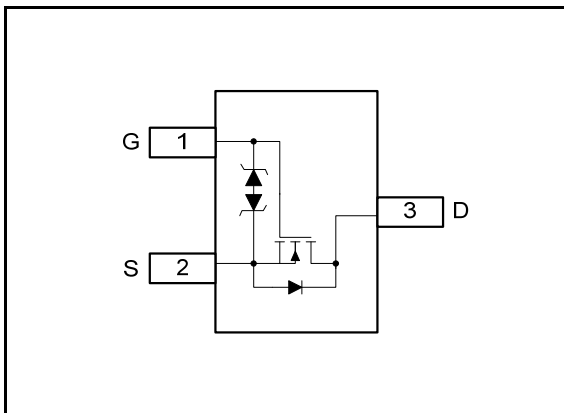
### Applications

- Battery Packs
- Battery-Powered Portable Equipments
- Cellular and Cordless Telephones

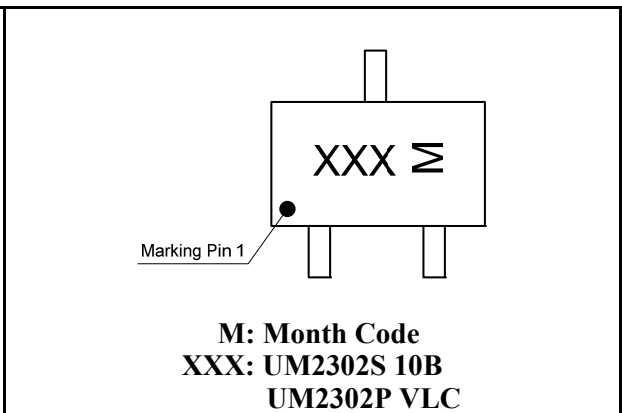
### Features

- Drain-Source Voltage (Max): 20V
- Low On-Resistance:  
 90mΩ@V<sub>GS</sub>=4.5V  
 150mΩ@V<sub>GS</sub>=2.5V
- Continuous Drain Current (Max):  
 2A@25°C (SOT23-3)  
 1.6A@25°C (SOT323)

### Pin Configurations



### Top View



### Ordering Information

Part Number	Packaging Type	Marking Code	Shipping Qty
UM2302S	SOT23-3	10B	3000pcs/7 Inch Tape & Reel
UM2302P	SOT323	VLC	

**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
V <sub>DSS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-Source Voltage	±8	V
I <sub>D</sub>	Continuous Drain Current (5s)	SOT23-3	2
		SOT323	1.6
I <sub>DP</sub>	Drain Current Pulsed (Pulse Width≤10μs, Duty Cycle≤1%)	5	A
P <sub>D</sub>	Power Dissipation	SOT23-3	0.86
		SOT323	0.5
T <sub>J</sub>	Junction Temperature	-55~150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (≤5s)	SOT23-3	145
		SOT323	250
ESD	ESD Method 3015.8	2000	V

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

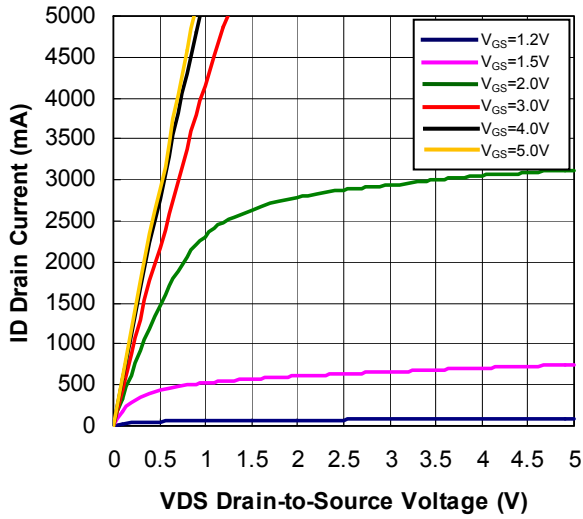
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			0.1	μA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
<b>On Characteristics</b>						
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance (Note 1)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.0A		90	150	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1.0A		150	200	
V <sub>GS(TH)</sub>	Gate-Source Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.40		0.90	V
g <sub>fs</sub>	Forward Transconductance (Note 1)	V <sub>DS</sub> =5V, I <sub>D</sub> =2A		4.5		S
<b>Dynamic Characteristics (Note 2)</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =10V, f=1.0MHz		150		pF
C <sub>oss</sub>	Output Capacitance			50		
C <sub>rss</sub>	Reverse Transfer Capacitance			40		
<b>Switching Characteristics (Note 2)</b>						
td(on)	Turn-on Delay Time	V <sub>DD</sub> =10V, R <sub>L</sub> =2.78Ω, I <sub>D</sub> =3.6A, V <sub>GEN</sub> =4.5V, R <sub>G</sub> =1Ω		8	15	ns
tr	Rise Time			10	25	
td(off)	Turn-off Delay Time			30	45	
tf	Fall Time			25	40	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
V <sub>SD</sub>	Forward Diode Voltage	I <sub>S</sub> =0.95A, V <sub>GS</sub> =0V		0.7	1.2	V

Note 1: Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%.

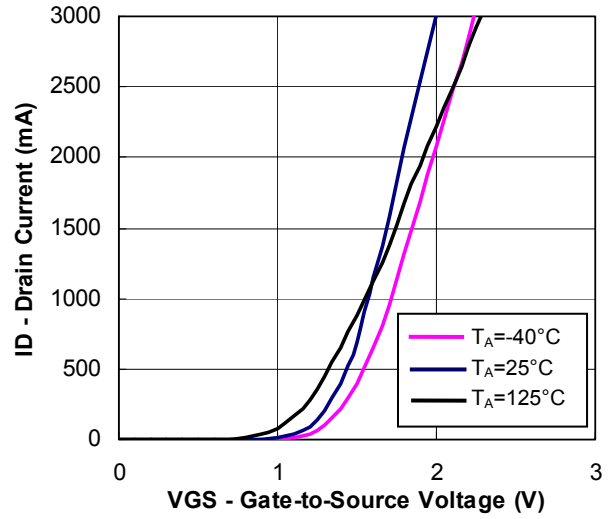
Note 2: Guaranteed by design, not subject to production testing.

## Typical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

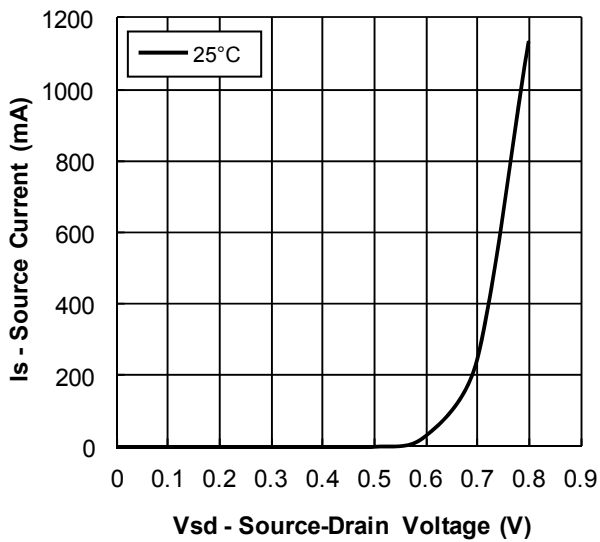
### Output Characteristics



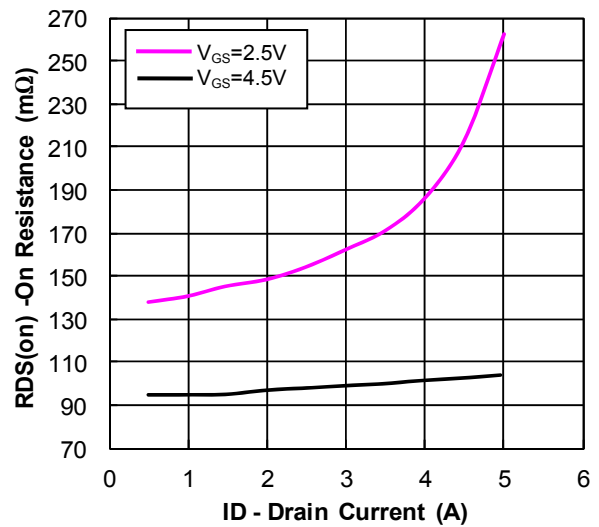
### Transfer Characteristics



### Source-Drain Diode Forward Voltage

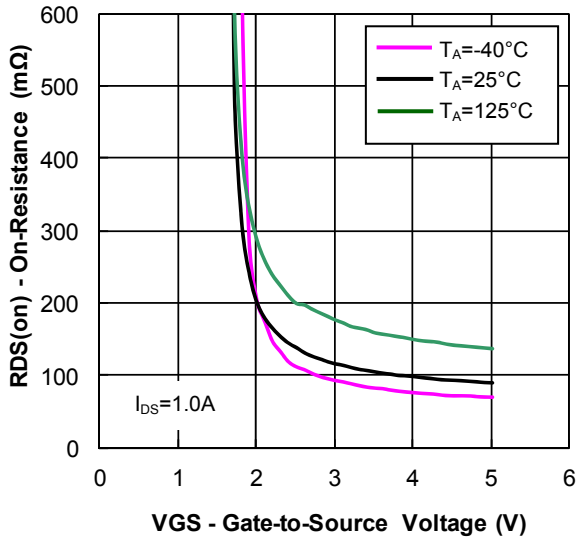


### On Resistance vs. Drain Current

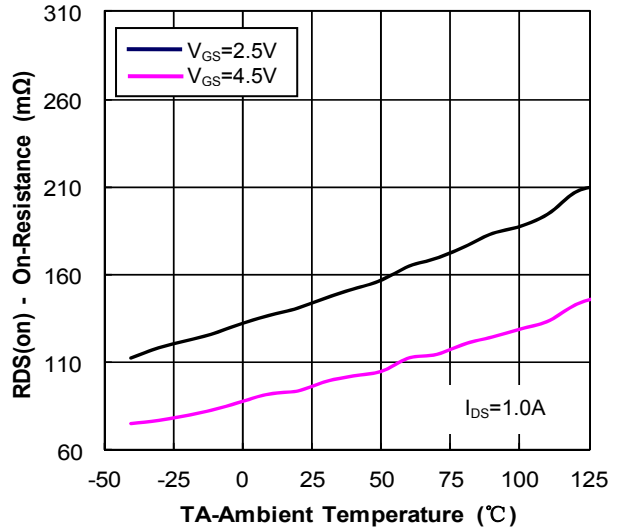


## Typical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

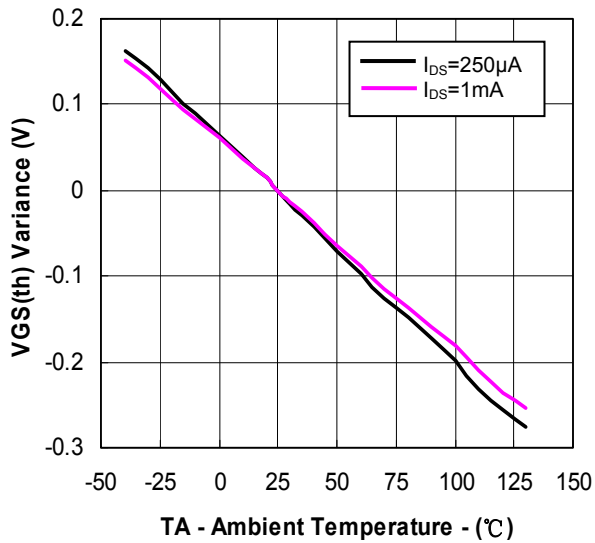
### On-Resistance vs. Gate-to-Source Voltage



### On-Resistance vs. Ambient Temperature



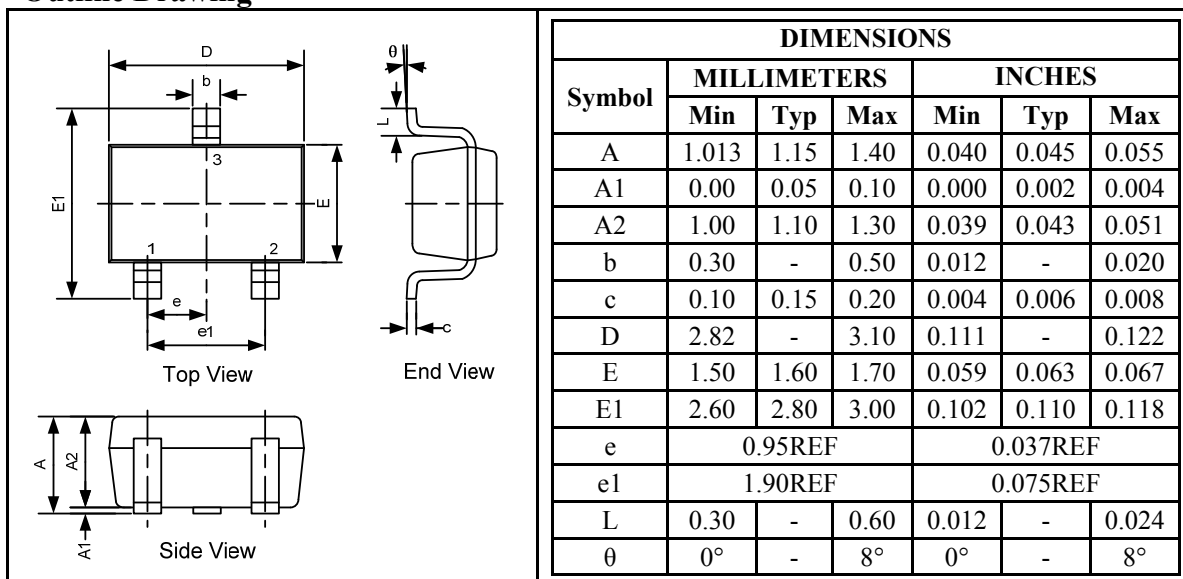
### Threshold Voltage vs. Ambient Temperature



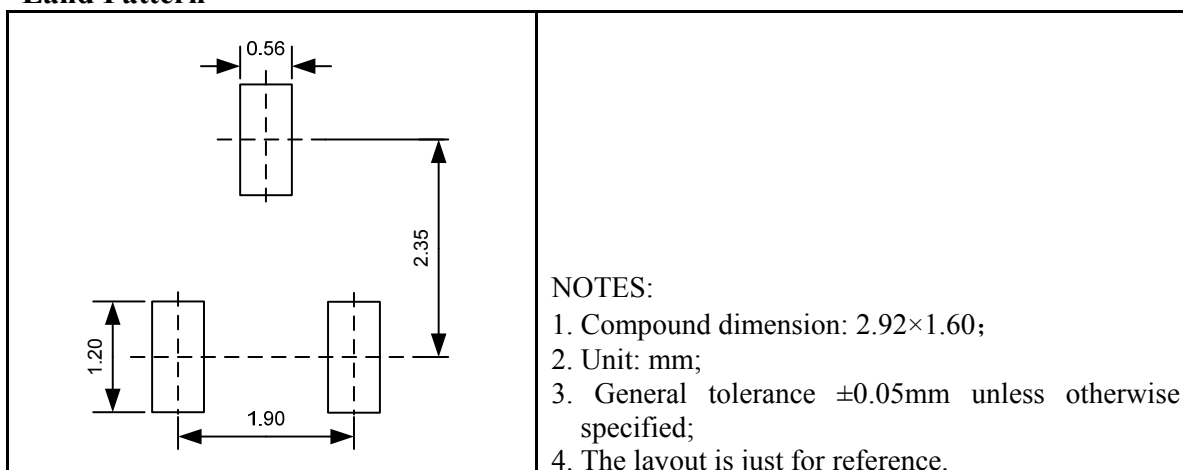
## Package Information

### UM2302S SOT23-3

#### Outline Drawing



#### Land Pattern

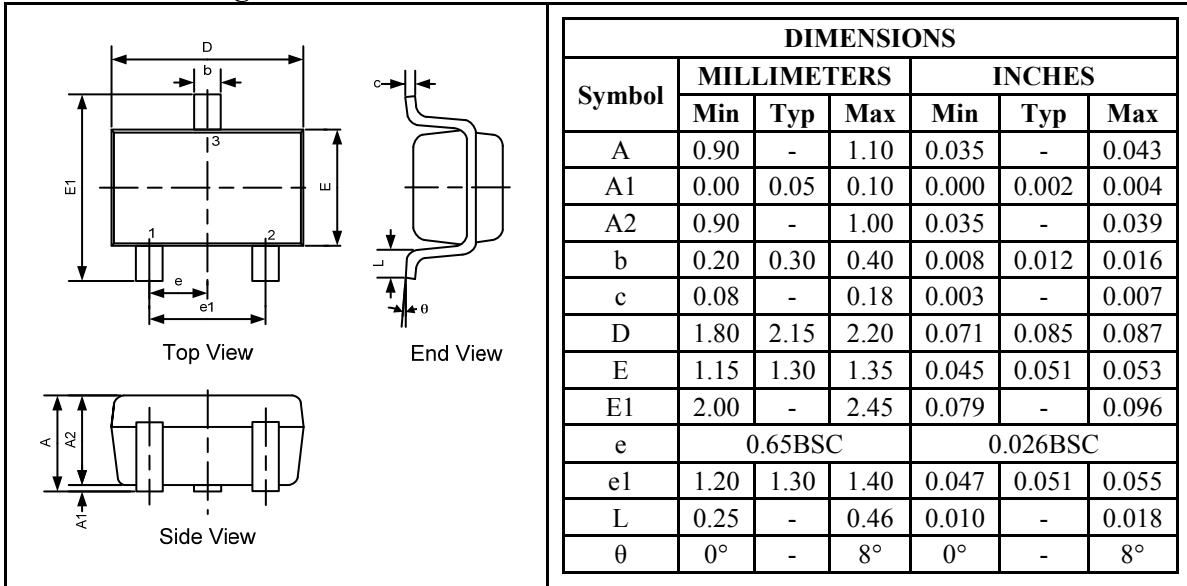


#### Tape and Reel Orientation

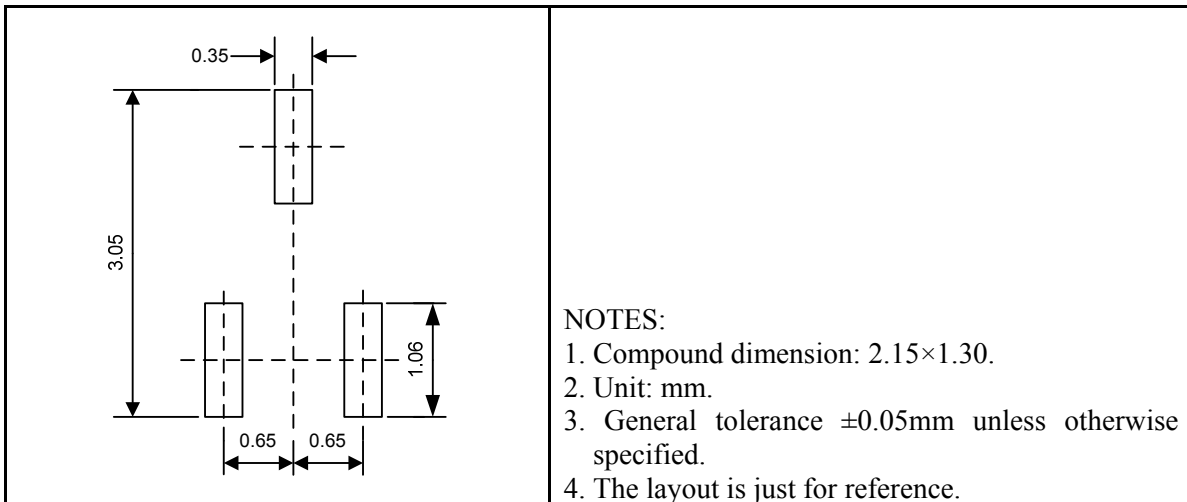


## UM2302P SOT323

### Outline Drawing



### Land Pattern



### Tape and Reel Orientation



---

## **GREEN COMPLIANCE**

Union Semiconductor is committed to environmental excellence in all aspects of its operations including meeting or exceeding regulatory requirements with respect to the use of hazardous substances. Numerous successful programs have been implemented to reduce the use of hazardous substances and/or emissions.

All Union components are compliant with the RoHS directive, which helps to support customers in their compliance with environmental directives. For more green compliance information, please visit:

[http://www.union-ic.com/index.aspx?cat\\_code=RoHSDeclaration](http://www.union-ic.com/index.aspx?cat_code=RoHSDeclaration)

## **IMPORTANT NOTICE**

The information in this document has been carefully reviewed and is believed to be accurate. Nonetheless, this document is subject to change without notice. Union assumes no responsibility for any inaccuracies that may be contained in this document, and makes no commitment to update or to keep current the contained information, or to notify a person or organization of any update. Union reserves the right to make changes, at any time, in order to improve reliability, function or design and to attempt to supply the best product possible.



Union Semiconductor, Inc

Add: Unit 606, No.570 Shengxia Road, Shanghai 201210

Tel: 021-51093966

Fax: 021-51026018

Website: [www.union-ic.com](http://www.union-ic.com)